2N4416, 2N4416A

N-Channel Silicon Junction Field-Effect Transistor

- Mixers
- VHF Amplifiers

Absolute maximum ratings at T_A = 25°C

Reverse Gate Source & Reverse Gate Drain Voltage	2N4416	– 30 V	2N4416A	– 35 V
Gate Current		10 mA		10 mA
Continuous Device Dissipation		300 mW		300 mW
Power Derating		2 mW°C		2 mW/°C

At 25°C free air temperature:		2N4416		2N4416A		Process NJ26		
Static Electrical Characteristics		**Min**	**Max**	**Min**	**Max**	**Unit**	**Test Conditions**	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	– 30		– 35		V	I_G = – 1µA, V_{DS} = ØV	
Gate Reverse Current	I_{GSS}		– 0.1		– 0.1	nA	V_{GS} = – 20V, V_{DS} = ØV	
			– 0.1		– 0.1	µA	V_{GS} = – 20V, V_{DS} = ØV	T_A = 150°C
Gate Source Cutoff Voltage	$V_{GS(OFF)}$		– 6	– 2.5	– 6	V	V_{DS} = 15V, I_D = 1 nA	
Drain Saturation Current (Pulsed)	I_{DSS}	5	15	5	15	mA	V_{DS} = 15V, V_{GS} = ØV	
Dynamic Electrical Characteristics								
Common Source Forward Transconductance	g_{fs}	4500	7500	4500	7500	µS	V_{DS} = 15V, V_{GS} = ØV	f = 1 kHz
		4000		4000		µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Output Conductance	g_{os}		50		50	µS	V_{DS} = 15V, V_{GS} = ØV	f = 1 kHz
			75		75	µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
			100		100	µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Input Capacitance	C_{iss}		4		4	pF	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz
Common Source Output Capacitance	C_{oss}		2		2	pF	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz
Common Source Reverse Transfer Capacitance	C_{rss}		0.8		0.8	pF	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz
Common Source Input Conductance	g_{is}		100		100	µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
			1000		1000	µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Input Susceptance	b_{is}		2500		2500	µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
			10000		10000	µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Output Susceptance	b_{os}		1000		1000	µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
			4000		4000	µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Power Gain	G_{ps}	18		18		dB	V_{DS} = 15V, I_D = 5mA	f = 100 MHz
		10		10		dB	V_{DS} = 15V, I_D = 5mA	f = 400 MHz
Noise Figure	NF		2		2	dB	V_{DS} = 15V, I_D = 5mA, R_G = 1kΩ	f = 100 MHz
			4		4	dB		f = 400 MHz

TO-72 Package
See Section G for Outline Dimensions

Surface Mount
SMP4416, SMP4416A

Pin Configuration
1 Source, 2 Drain, 3 Gate, 4 Case

Note: rf parameters guaranteed, but not 100% tested.

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2N5484, 2N5485, 2N5486

N-Channel Silicon Junction Field-Effect Transistor

- VHF/UHF Amplifiers

Absolute maximum ratings at T_A = 25°C

Reverse Gate Source Voltage	– 25 V
Reverse Gate Drain Voltage	– 25 V
Continuous Device Power Dissipation	360 mW
Power Derating	3.27 mW/°C

At 25°C free air temperature: Static Electrical Characteristics		2N5484		2N5485		2N5486		Process NJ26		
		Min	Max	Min	Max	Min	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	– 25		– 25		– 25		V	I_G = 1µA, V_{DS} = ØV	
Gate Reverse Current	I_{GSS}		– 1		– 1		– 1	nA	V_{GS} = – 20V, V_{DS} = ØV	
			– 0.2		– 0.2		– 0.2	µA	V_{GS} = – 20V, V_{DS} = ØV	T_A = 100°C
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	– 0.3	– 3	– 0.5	– 4	– 2	– 6	V	V_{DS} = 15V, I_D = 10 nA	
Drain Saturation Current (Pulsed)	I_{DSS}	1	5	4	10	8	20	mA	V_{DS} = 15V, V_{GS} = ØV	
Dynamic Electrical Characteristics										
Forward Transconductance	$R_{e(Yfs)}$	2500						µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
				3000		3500		µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Forward Transadmittance	Y_{fs}	3000	6000	3500	7000	4000	8000	µS	V_{DS} = 15V, V_{GS} = ØV	f = 1 kHz
Input Admittance	$R_{e(Yis)}$		100					µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
					1000		1000	µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Output Conductance	$R_{e(Yos)}$		75					µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
					100		100	µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Output Admittance	Y_{os}		50		60		75	µS	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz
Common Source Input Capacitance	C_{iss}		5		5		5	pF	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz
Common Source Reverse Transfer Capacitance	C_{rss}		1		1		1	pF	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz
Output Capacitance	C_{oss}		2		2		2	pF	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz

TO-226AA Package
Dimensions in Inches (mm)

Pin Configuration
1 Drain, 2 Source, 3 Gate

Surface Mount
SMP5484, SMP5485, SMP5486

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IFN5911, IFN5912

N-Channel Dual Silicon Junction Field-Effect Transistor

- VHF Amplifiers
- Wideband Differential Amplifiers

Absolute maximum ratings at T_A = 25°C

Continuous Forward Gate Current	50 mA
Continuous Device Power Dissipation	500 mW
Power Derating	4 mW/°C
Storage Temperature Range	– 65°C to 200°C

At 25°C free air temperature:		IFN5911		IFN5912		Process NJ30L or NJ36D		
Static Electrical Characteristics		**Min**	**Max**	**Min**	**Max**	**Unit**	**Test Conditions**	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	– 25		– 25		V	I_G = – 1 µA, V_{DS} = ØV	
Gate Reverse Current	I_{GSS}		– 100		– 100	pA	V_{GS} = – 15V, V_{DS} = ØV	
			– 250		– 250	nA	V_{GS} = – 15V, V_{DS} = ØV	T_A = 150°C
Gate Operating Current	I_G		– 100		– 100	pA	V_{DG} = 10V, I_D = 5 mA	
			– 100		– 100	nA	V_{DG} = 10V, I_D = 5 mA	T_A = 125°C
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	– 1	– 5	– 1	– 5	V	V_{DS} = 10V, I_D = 1 nA	
Gate Source Voltage	V_{GS}	– 0.3	– 4	– 0.3	– 4	V	V_{DS} = 10V, I_D = 5 mA	
Drain Saturation Current (Pulsed)	I_{DSS}	7	40	7	40	mA	V_{DS} = 10V, V_{GS} = ØV	
Dynamic Electrical Characteristics								
Common Source Forward Transconductance	g_{fs}	3000	10000	3000	10000	µS	V_{DG} = 10V, I_D = 5 mA	f = 1 kHz
		3000	10000	3000	10000	µS	V_{DG} = 10V, I_D = 5 mA	f = 100 MHz
Common Source Output Conductance	g_{os}		100		100	µS	V_{DG} = 10V, I_D = 5 mA	f = 1 kHz
			150		150	µS	V_{DG} = 10V, I_D = 5 mA	f = 100 MHz
Common Source Input Capacitance	C_{iss}		5		5	pF	V_{DG} = 10V, I_D = 5 mA	f = 1 MHz
Common Source Reverse Transfer Capacitance	C_{rss}		1.2		1.2	pF	V_{DG} = 10V, I_D = 5 mA	f = 1 MHz
Equivalent Short Circuit Input Noise Voltage	$\bar{e}_N$		20		20	nV/√Hz	V_{DG} = 10V, I_D = 5 mA	f = 10 kHz
Noise Figure	NF		1		1	dB	V_{DG} = 10V, I_D = 5 mA R_G = 100 KΩ	f = 10 Hz
Differential Gate Current	$\lvert I_{G1}\rvert - \lvert I_{G2}\rvert$		20		20	nA	V_{DG} = 10V, I_D = 5 mA	T_A = 125°C
Saturation Drain Current Ratio	I_{DSS1}/I_{DSS2}	0.95	1	0.95	1		V_{DS} = 10V, V_{GS} = ØV	
Differential Gate Source Voltage	$V_{GS1} - V_{GS2}$		10		15	mV	V_{DG} = 10V, I_D = 5 mA	
Gate Source Voltage Differential Drift	$\frac{\Delta V_{GS1} - V_{GS2}}{\Delta T}$		20		40	µV/°C	V_{DG} = 10V, I_D = 5 mA	T_A = 25°C T_B = 125°C
	$\frac{\Delta V_{GS1} - V_{GS2}}{\Delta T}$		20		40	µV/°C	V_{DG} = 10V, I_D = 5 mA	T_A = – 55°C T_B = 25°C
Transconductance Ratio	g_{fs1}/g_{fs2}	0.95	1	0.95	1		V_{DG} = 10V, I_D = 5 mA	f = 1 kHz

TO-78 Package

See Section G for Outline Dimensions

Pin Configuration

1 Source, 2 Drain, 3 Gate, 4 Case,
5 Source, 6 Drain, 7 Gate, 8 Omitted

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J304, J305

N-Channel Silicon Junction Field-Effect Transistor

- Mixers
- Oscillators
- VHF/UHF Amplifiers

Absolute maximum ratings at T_A = 25°C

Reverse Gate Source & Reverse Gate Drain Voltage	– 30 V
Continuous Forward Gate Current	10 mA
Continuous Device Power Dissipation	360 mW
Power Derating	3.27 mW/°C

At 25°C free air temperature: Static Electrical Characteristics		J304			J305			Process NJ26		
		Min	Typ	Max	Min	Typ	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	– 30			– 30			V	I_G = – 1µA, V_{DS} = ØV	
Gate Reverse Current	I_{GSS}			– 100			– 100	pA	V_{GS} = – 20V, V_{DS} = ØV	
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	– 2		– 6	– 0.5		– 3	V	V_{DS} = 15V, I_D = 1 nA	
Drain Saturation Current (Pulsed)	I_{DSS}	5		15	1		8	mA	V_{DS} = 15V, V_{GS} = ØV	
Dynamic Electrical Characteristics										
Common Source Forward Transconductance	g_{fs}	4500		7500	3000			µS	V_{DS} = 15V, V_{GS} = ØV	f = 1 kHz
						3000		µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
			4200					µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Output Conductance	g_{os}			50			50	µS	V_{DS} = 15V, V_{GS} = ØV	f = 1 kHz
Common Source Input Capacitance	C_{iss}		3			3		pF	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz
Common Source Reverse Transfer Capacitance	C_{rss}		0.85			0.85		pF	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz
Common Source Output Capacitance	C_{oss}		1			1		pF	V_{DS} = 15V, V_{GS} = ØV	f = 1 MHz
Common Source Output Conductance	g_{os}		60			60		µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
			80					µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Output Susceptance	b_{os}		800			800		µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
			3600					µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Input Conductance	g_{is}		80			80		µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
			800					µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Input Susceptance	b_{is}		2000			2000		µS	V_{DS} = 15V, V_{GS} = ØV	f = 100 MHz
			7500					µS	V_{DS} = 15V, V_{GS} = ØV	f = 400 MHz
Common Source Power Gain	G_{ps}		20					dB	V_{DS} = 15V, I_D = 5 mA	f = 100 MHz
			11					dB	V_{DS} = 15V, I_D = 5 mA	f = 400 MHz
Noise Figure	NF		1.7					dB	V_{DS} = 15V, I_D = 5 mA R_G = 1 Ω	f = 100 MHz
			3.8					dB		f = 400 MHz

TO-226AA Package
Dimensions in Inches (mm)

Pin Configuration
1 Drain, 2 Source, 3 Gate

Surface Mount
SMPJ304, SMPJ305

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J308, J309

N-Channel Silicon Junction Field-Effect Transistor

- Mixers
- Oscillators
- VHF/UHF Amplifiers

Absolute maximum ratings at T_A = 25°C

Reverse Gate Source & Reverse Gate Drain Voltage	– 25 V
Continuous Forward Gate Current	10 mA
Continuous Device Power Dissipation	360 mW
Power Derating	3.27 mW/°C

At 25°C free air temperature: Static Electrical Characteristics		J308			J309			Process NJ72		
		Min	Typ	Max	Min	Typ	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	– 25			– 25			V	I_G = – 1µA, V_{DS} = ØV	
Gate Reverse Current	I_{GSS}			– 1			– 1	nA	V_{GS} = – 15V, V_{DS} = ØV	
				– 1			– 1	µA	V_{GS} = – 15V, V_{DS} = ØV	T_A = +125°C
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	– 1		– 6.5	– 1		– 4	V	V_{DS} = 10V, I_D = 1 nA	
Gate Source Forward Voltage	$V_{GS(F)}$			1			1	V	V_{DS} = ØV, I_G = 1 mA	
Drain Saturation Current (Pulsed)	I_{DSS}	12		60	12		30	mA	V_{DS} = 10V, V_{GS} = ØV	
Dynamic Electrical Characteristics										
Common Source Forward Transconductance	g_{fs}	8000	17000		10000	17000		µS	V_{DS} = 10V, I_D = 10 mA	f = 1 kHz
Common Source Output Conductance	g_{os}			250			250	µS	V_{DS} = 10V, I_D = 10 mA	f = 1 kHz
Common Gate Forward Transconductance	g_{fg}		13000			13000		µS	V_{DS} = 10V, I_D = 10 mA	f = 1 kHz
Common Gate Output Transconductance	g_{og}		150			100		µS	V_{DS} = 10V, I_D = 10 mA	f = 1 kHz
Gate Drain Capacitance	C_{dg}		1.8	2.5		1.8	2.5	pF	V_{DS} = ØV, V_{GS} = – 10V	f = 1 MHz
Gate Source Capacitance	C_{gs}		4	5		4	5	pF	V_{DS} = ØV, V_{GS} = – 10V	f = 1 MHz
Equivalent Short Circuit Input Noise Voltage	$\bar{e}_N$		10			10		nV/√Hz	V_{DS} = 10V, I_D = 10 mA	f = 100 kHz
Common Source Forward Transconductance	$Re_{(Yfs)}$		12			12		µS	V_{DS} = 10V, I_D = 10 mA	f = 105 MHz
Common Gate Input Conductance	$Re_{(Yig)}$		14			14		µS	V_{DS} = 10V, I_D = 10 mA	f = 105 MHz
Common Source Input Conductance	$Re_{(Yis)}$		0.4			0.4		µS	V_{DS} = 10V, I_D = 10 mA	f = 105 MHz
Common Source Output Conductance	$Re_{(Gos)}$		0.15			0.15		µS	V_{DS} = 10V, I_D = 10 mA	f = 105 MHz
Common Gate Power Gain at Noise Match	G_{pg}		16			16		dB	V_{DS} = 10V, I_D = 10 mA	f = 105 MHz
			11			11		dB	V_{DS} = 10V, I_D = 10 mA	f = 450 MHz
Noise Figure	NF		1.5			1.5		dB	V_{DS} = 15V, I_D = 10 mA	f = 105 MHz
			2.7			2.7		dB	V_{DS} = 15V, I_D = 10 mA	f = 450 MHz

TO-226AA Package
Dimensions in Inches (mm)

Pin Configuration
1 Drain, 2 Source, 3 Gate

Surface Mount
SMPJ308, SMPJ309

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J310

N-Channel Silicon Junction Field-Effect Transistor

- Mixer
- Oscillator
- VHF/UHF Amplifier

Absolute maximum ratings at T_A = 25°C

Reverse Gate Source Voltage	– 25 V
Reverse Gate Drain Voltage	– 25 V
Continuous Forward Gate Current	10 mA
Continuous Device Power Dissipation	360 mW

At 25°C free air temperature:		J310			Process NJ72		
Static Electrical Characteristics		**Min**	**Typ**	**Max**	**Unit**	**Test Conditions**	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	– 25			V	I_G = – 1 µA, V_{DS} = ØV	
Gate Reverse Current	I_{GSS}			– 1	nA	V_{GS} = – 15V, V_{DS} = ØV	
				– 1	µA	V_{GS} = – 15V, V_{DS} = ØV	T_A = + 125°C
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	– 2		– 6.5	V	V_{DS} = 10V, I_D = 1 nA	
Gate Source Forward Voltage	$V_{GS(F)}$			1	V	V_{DS} = ØV, I_G = 1 mA	
Drain Saturation Current (Pulsed)	I_{DSS}	24		60	mA	V_{DS} = 10V, V_{GS} = ØV	
Dynamic Electrical Characteristics							
Common Source Forward Transconductance	g_{fs}	8000	17000		µS	V_{DS} = 10V, I_D = 10 mA	f = 1 kHz
Common Source Output Conductance	g_{os}			250	µS	V_{DS} = 10V, I_D = 10 mA	f = 1 kHz
Common Gate Forward Transconductance	g_{fg}		1200		µS	V_{DS} = 10V, I_D = 10 mA	f = 1 kHz
Common Gate Output Transconductance	g_{og}		150		µS	V_{DS} = 10V, I_D = 10 mA	f = 1 kHz
Gate Drain Capacitance	C_{dg}		1.8	2.5	pF	V_{DS} = ØV, V_{GS} = – 10V	f = 1 MHz
Gate Source Capacitance	C_{gs}		4	5	pF	V_{DS} = ØV, V_{GS} = – 10V	f = 1 MHz
Equivalent Short Circuit Input Noise Voltage	$\bar{e}_N$		10		nV/√Hz	V_{DS} = 10V, I_D = 10 mA	f = 100 Hz
Common Source Forward Transconductance	Re (Y_{fs})		12		µS	V_{DS} = 10V, I_D = 10 mA	f = 105 MHz
Common Gate Input Conductance	Re (Y_{ig})		14		µS	V_{DS} = 10V, I_D = 10 mA	f = 105 MHz
Common Source Input Conductance	Re (Y_{is})		0.4		µS	V_{DS} = 10V, I_D = 10 mA	f = 105 MHz
Common Source Output Conductance	Re (g_{os})		0.15		µS	V_{DS} = 10V, I_D = 10 mA	f = 105 MHz
Common Gate Power Gain at Noise Match	G_{pg}		16		dB	V_{DS} = 10V, I_D = 10 mA	f = 105 MHz
			11		dB	V_{DS} = 10V, I_D = 10 mA	f = 450 MHz
Noise Figure	NF		1.5		dB	V_{DS} = 15V, I_D = 10 mA	f = 105 MHz
			2.7		dB	V_{DS} = 15V, I_D = 10 mA	f = 450 MHz

TO-226AA Package
Dimensions in Inches (mm)

Pin Configuration
1 Drain, 2 Source, 3 Gate

Surface Mount
SMPJ310

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U430, U431

Dual N-Channel Silicon Junction Field-Effect Transistor

- Balanced Mixers
- Differential Amplifiers

Absolute maximum ratings at T_A = 25°C.

Total Device Dissipation (Derate 4 mW/°C to150°C)	500 mW
Storage Temperature Range	– 65°C to +150°C
Lead Temperature	300°C

At 25°C free air temperature: Static Electrical Characteristics		U430			U431			Process NJ72		
		Min	Typ	Max	Min	Typ	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	– 25			– 25			V	I_G = – 1µA, V_{DS} = ØV	
Gate Reverse Current	I_{GSS}			– 150			– 150	pA	V_{GS} = – 15V, V_{DS} = ØV	
				– 150			– 150	nA	V_{GS} = – 15V, V_{DS} = ØV	T_A = 150°C
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	– 1		– 4	– 2		– 6	V	V_{DS} = 10V, I_D = 1 nA	
Gate Source Forward Voltage	$V_{GS(F)}$			1			1	V	V_{DS} = ØV, I_G = 10 mA	
Drain Saturation Current (Pulsed)	I_{DSS}	12		30	24		60	mA	V_{DS} = 10V, V_{GS} = ØV	
Dynamic Electrical Characteristics										
Common Source Forward Transconductance	G_{fs}	10	17		10	17		mS	V_{DS} = 10V, I_D = 10 mA	f = 1 kHz
			12			12		mS	V_{DS} = 10V, I_D = 10 mA	f = 100 MHz
Common Source Output Conductance	G_{os}			250			250	µS	V_{DS} = 10V, I_D = 10 mA	f = 1 kHz
			0.15			0.15		µS	V_{DS} = 10V, I_D = 10 mA	f = 100 MHz
Drain Gate Capacitance	C_{dg}			5			5	pF	V_{DS} = ØV, V_{GS} = – 10V	f = 1 MHz
Source Gate Capacitance	C_{gs}			2.5			2.5	pF	V_{DS} = ØV, V_{GS} = – 10V	f = 1 MHz
Equivalent Short Circuit Input Noise Voltage	$\bar{e}_N$		10			10		nV/√Hz	V_{DS} = 10V, I_D = 10 mA	f = 100 kHz
Power Match Source Admittance	g_{ig}		12			12			V_{DS} = 10V, I_D = 10 mA	f = 100 MHz
Conversion Gain	G_c		3			3		dB	V_{DS} = 20V, R_L = 2 kΩ V_{GS} = 1/2 $V_{GS(OFF)}$	f = 100 MHz
Saturation Drain Current Ratio	I_{DSS1}/I_{DSS2}	0.9		1	0.9		1		V_{DS} = 10V, V_G = ØV	
Gate Source Cutoff Voltage Ratio	$\frac{V_{GS(OFF)1}}{V_{GS(OFF)2}}$	0.9		1	0.9		1		V_{DS} = 10V, I_D = 1 nA	
Transconductance Ratio	g_{fs1}/g_{fs2}	0.9		1	0.9		1		V_{DS} = 10V, I_D = 10 mA	

TO-78 Package
Dimensions in Inches (mm)

Pin Configuration
1 Source 1, 2 Gate 1, Drain 1,
4 Case, 5 Drain 2, 6 Gate 2,
7 Source 2, 8 Omitted

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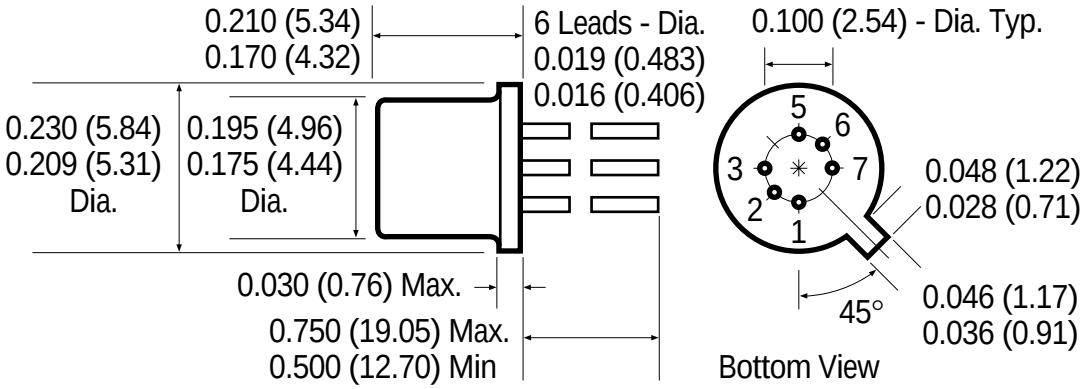
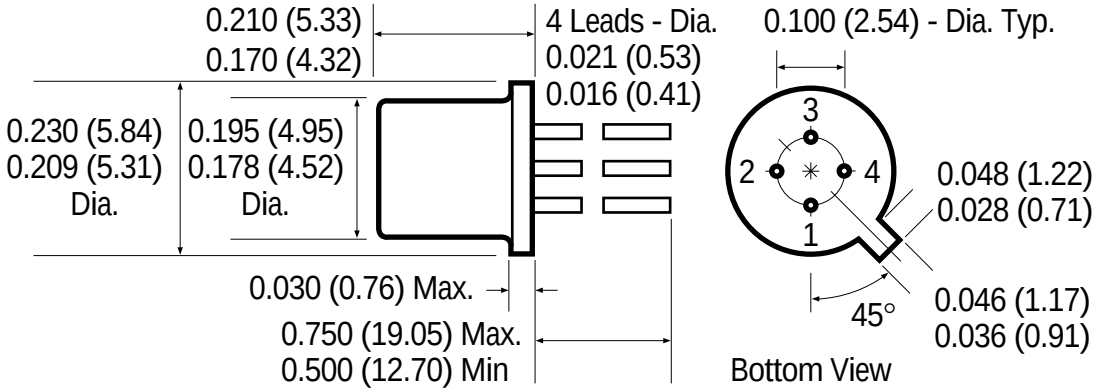
TO-71 Package

Dimensions in Inches (mm)



TO-72 Package

Dimensions in Inches (mm)



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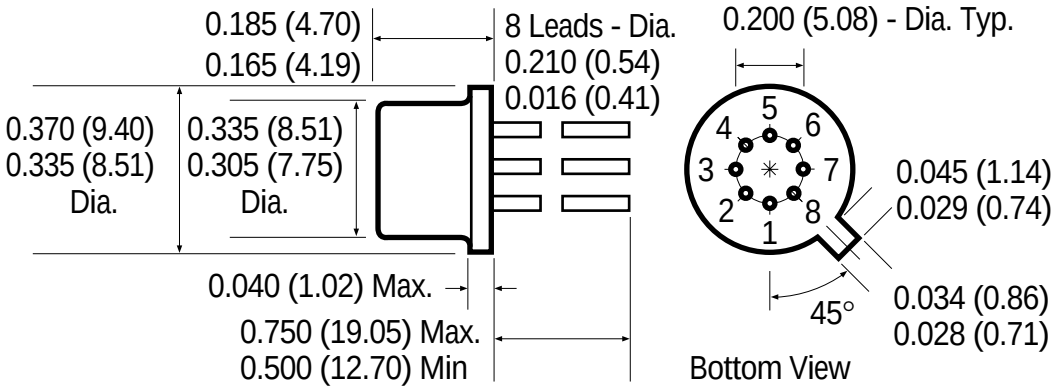
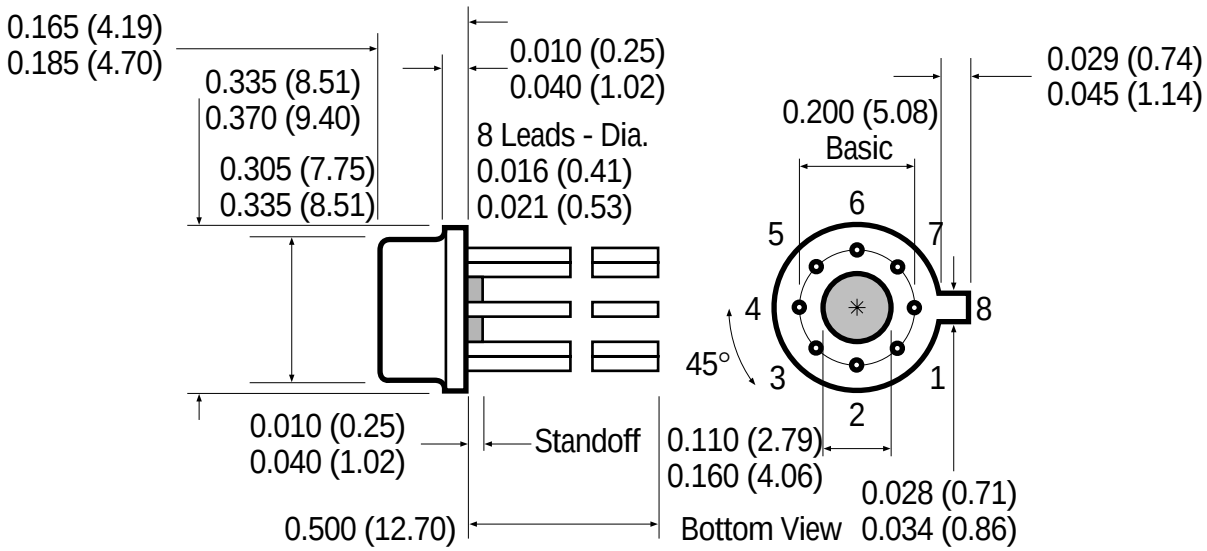
TO-78 Package

Dimensions in Inches (mm)



TO-99 Package

Dimensions in Inches (mm)



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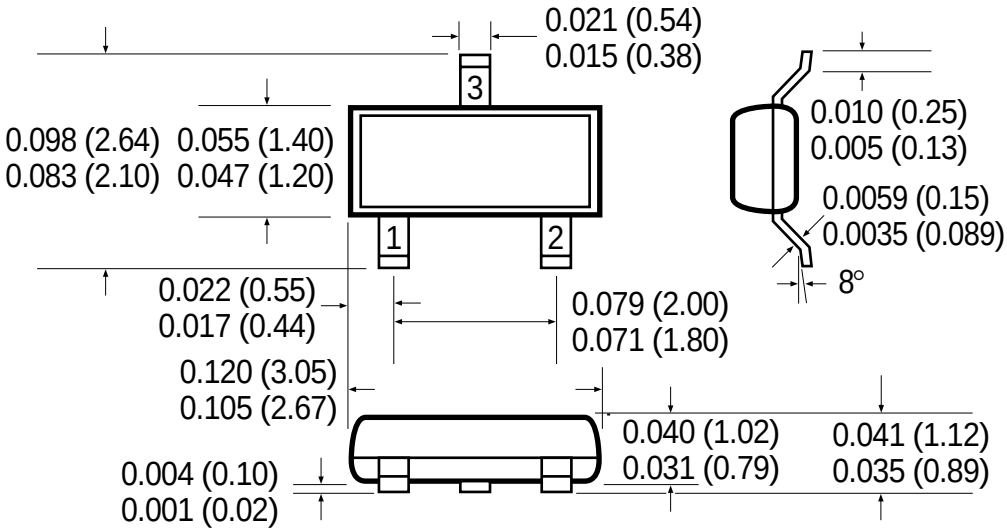
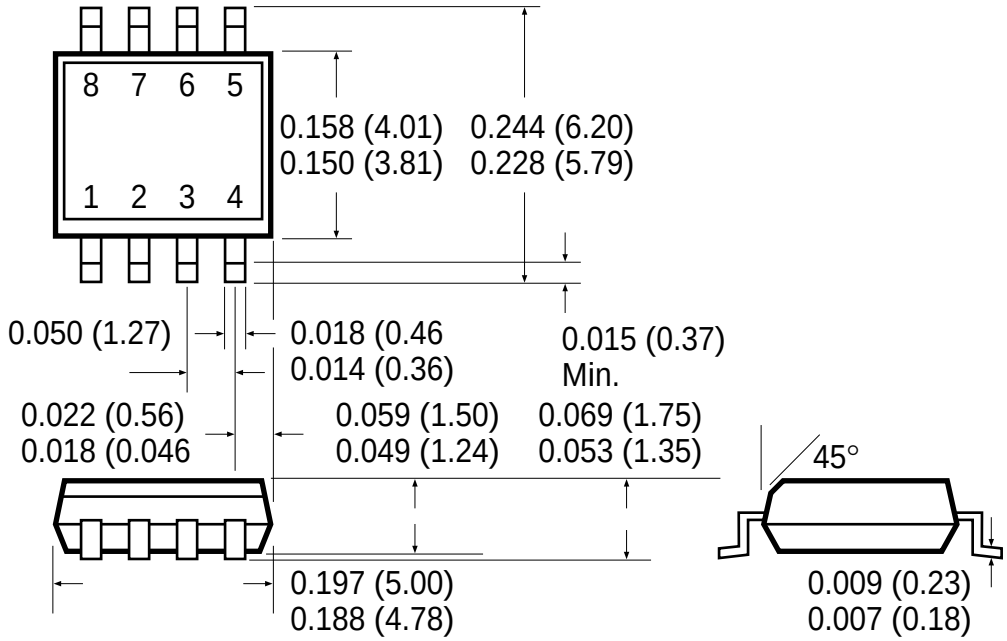
TO-236AB Package (SOT-23)

Dimensions in Inches (mm)



SOIC-8 Package

Dimensions in Inches (mm)



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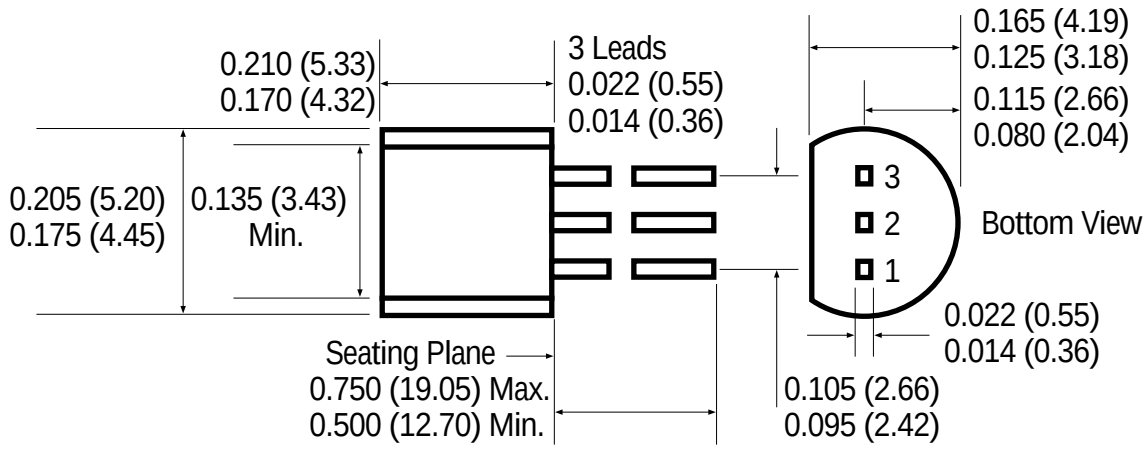
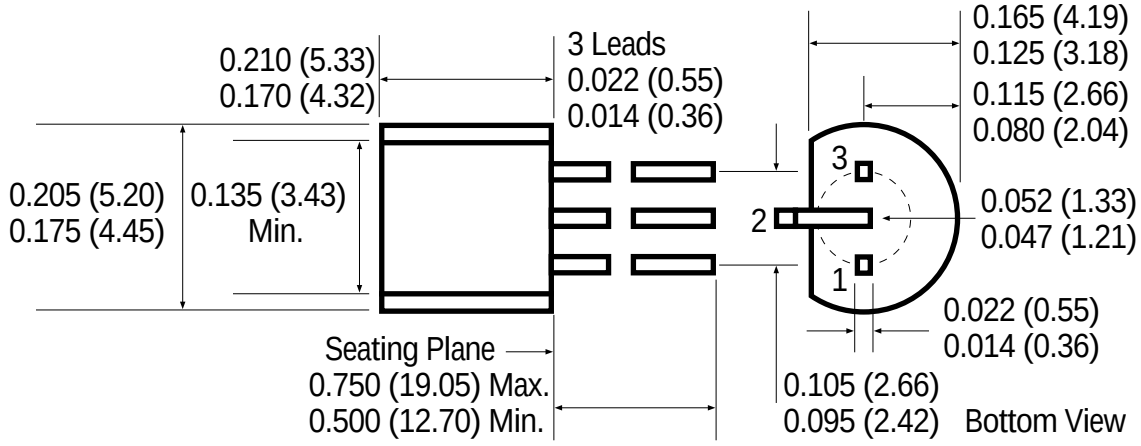
TO-226AA Package (TO-92)

Dimensions in Inches (mm)



TO-226AB Package (TO-92/18)

Dimensions in Inches (mm)



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